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Features

- Wide operating frequency range up to (150kHz)
- Pulse by pulse over current limiting
- Over load protection
- Over voltage protecton (Min. 23V)

FAIRCHILD

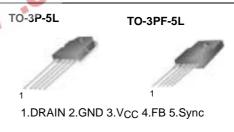
SEMICONDUCTOR

- Internal thermal shutdown function
- Under voltage lockout
- Internal high voltage sense FET
- External sync terminal
- Auto Restart Mode

Description

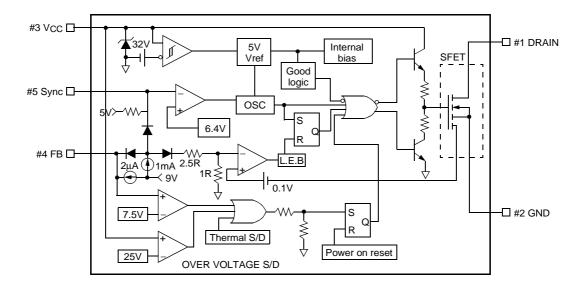
The Fairchild Power Switch(FPS) product family is specially designed for an off line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. controller IC features a trimmed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit. compared to discrete MOSFET and controller or RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency,

productivity, and system reliability. It has a basic platform well suited for cost effective C-TV power supply.





Internal Block Diagram



Absolute Maximum Ratings

VD,MAX		
•	800	V
Vdgr	800	V
Vgs	±30	V
IDM	24.0	ADC
EAS	455	mJ
ID	6.0	ADC
ID	4.0	ADC
VCC,MAX	30	V
VFB	–0.3 to V _{SD}	V
P _D (watt H/S)	150	W
Derating	1.21	W/°C
TA	-25 to +85	°C
TSTG	-55 to +150	°C
	VGS IDM EAS ID ID VCC,MAX VFB PD (watt H/S) Derating TA	VGS ±30 IDM 24.0 EAS 455 ID 6.0 ID 4.0 VCC,MAX 30 VFB -0.3 to VSD PD (watt H/S) 150 Derating 1.21 TA -25 to +85

1. Tj=25°C to 150°C

an juni 2. Repetitive rating: Pulse width limited by maximum junction temperature

3. L=24mH, starting Tj=25 °C

Electrical Characteristics (SFET part)

(Ta = 25° C unless otherwise specified)

Characteristic	Symbol	Test condition	Min.	Тур.	Max.	Unit
Drain source breakdown voltage	BVDSS	$VGS = 0V, ID = 50\mu A$	800	-	-	V
Zero gate voltage drain current	IDSS VGS =	V _{DS} = Max., Rating, V _{GS} = 0V	-	-	50	μΑ
		V _{DS} = 0.8Max., Rating, V _{GS} = 0V, T _C = 125°C	-	-	200	mA
Static drain source on resistance (note)	RDS(ON)	$V_{GS} = 10V, I_{D} = 4.0A$	-	1.6	2.0	W
Forward transconductance (note)	gfs	VDS = 15V, ID = 4.0A	1.5	2.5	-	S
Input capacitance	Ciss		-	1600	-	
Output capacitance	Coss	VGS = 0V, VDS = 25V, f = 1MHz	-	140	-	pF
Reverse transfer capacitance	Crss		-	42	-	
Turn on delay time	td(on)	VDD= 0.5BVDSS, ID= 6.0A (MOSFET switching time are essentially	-	60	-	
Rise time	tr		-	150	-	•
Turn off delay time	td(off)		-	300	-	nS
Fall time	tf	independent of operating temperature)	-	130	-	
Total gate charge (gate-source+gate-drain)	Qg	VGS =10V, ID = 6.0A, VDS = 0.5BVDSS (MOSFET	-	70	-	
Gate source charge	Qgs	switching time are	-	16	-	nC
Gate drain (Miller) charge	Qgd	essentially independent of operating temperature)	-	27	-	

 $\sum_{i=1}^{n}$

Note:

Pulse test: Pulse width $\leq 300\mu$ S, duty cycle $\leq 2\%$

 $S \;=\; \frac{1}{R}$

Electrical Charcteristics (SFET part) (Continued)

(Ta = 25°C unless otherwise specified)

Characteristic	Symbol	Test condition	Min.	Тур.	Max.	Unit
UVLO SECTION		•	1		1	<u>I</u>
Start threshold voltage	VSTART	-	14	15	16	V
Stop operating voltage	VSTOP	After turn on	9	10	11	V
OSCILLATOR SECTION		1	1		1	
Initial accuracy	Fosc	Ta = 25°C	18	20	22	kHz
Frequency change with temperature ⁽²⁾	$\Delta F / \Delta T$	–25°C ≤ Ta ≤ +85°C	-	±5	±10	%
Maximum duty cycle	DMAX	-	92	95	98	%
FEEDBACK SECTION		1	1			
Feedback source current	IFB	Ta = 25°C, Vfb = GND	0.7	0.9	1.1	mA
Shutdown Feedback voltage	VSD	-	6.9	7.5	8.1	V
Shutdown delay current	Idelay	Ta = 25° C, 5 V \leq Vfb \leq V _{SD}	1.4	1.8	2.2	μA
SYNC. & SOFT START SECTION			1		1	
Soft start voltage	Vss	VFB = 2V	4.7	5.0	5.3	V
Soft start current	Iss	Sync & S/S = GND	0.8	1.0	1.2	mA
Sync threshold voltage ⁽³⁾	Vsyth	Vfb = 5V	6.0	6.4	6.8	V
REFERENCE SECTION		23 6			1	
Output voltage ⁽¹⁾	Vref	Ta = 25°C	4.80	5.00	5.20	V
Temperature Stability ⁽¹⁾⁽²⁾	Vref/ A T	_25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C
CURRENT LIMIT (SELF-PROTECTION) SECTION		•			
Peak Current Limit	IOVER	Max. inductor current	3.52	4.00	4.48	A
PROTECTION SECTION			•			
Thermal shutdown temperature (Tj) ⁽¹⁾	TSD	-	140	160	-	°C
Over voltage protection voltage	VOVP	-	23	25	28	V
TOTAL DEVICE SECTION		1	1		1	
Start Up current	ISTART	V _{CC} = 14V	0.1	0.3	0.55	mA
Operating supply current (control part only)	IOP	Ta = 25°C	6	12	18	mA
VCC zener voltage	Vz	ICC = 20mA	30	32.5	35	V

Note:

1. These parameters, although guaranteed, are not 100% tested in production

2. These parameters, although guaranteed, are tested in EDS(water test) process

3. The amplitude of the sync. pulse is recommended to be between 2V and 3V for stable sync. function.

Typical Performance Characteristics (control part)

(These characteristic graphs are normalized at $Ta = 25^{\circ}C$)

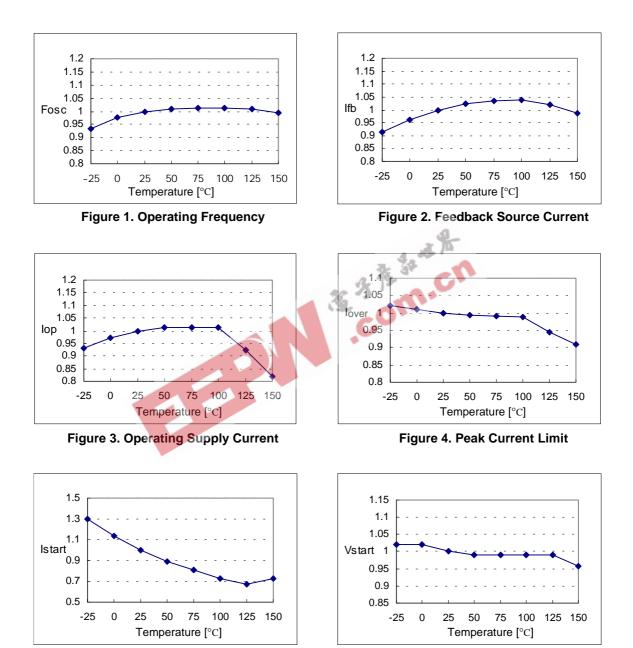


Figure 5. Start up Current



Typical Performance Characteristics (continued)

(These characteristic graphs are normalized at $Ta = 25^{\circ}C$)

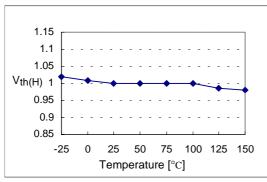


Figure 7. Stop Threshold Voltage

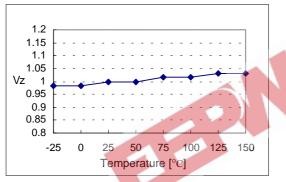


Figure 9. Vcc Zener Voltage

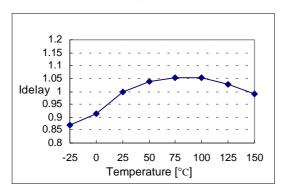


Figure 11. Shutdown Delay Current

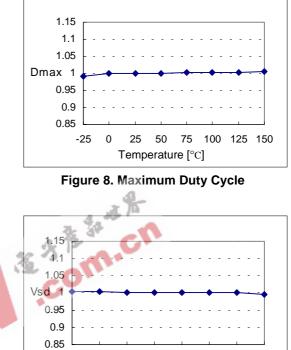


Figure 10. Shutdown Feedback Voltage

50

Temperature [°C]

75

100 125 150

-25

0

25

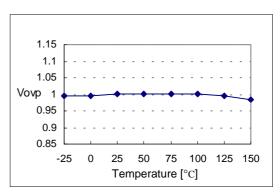


Figure 12. Over Voltage Protection

Typical Performance Characteristics (continued)

(These characteristic graphs are normalized at Ta = 25° C)

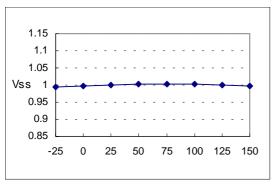


Figure13. Soft Start Voltage

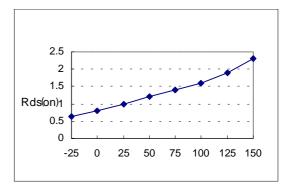
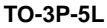
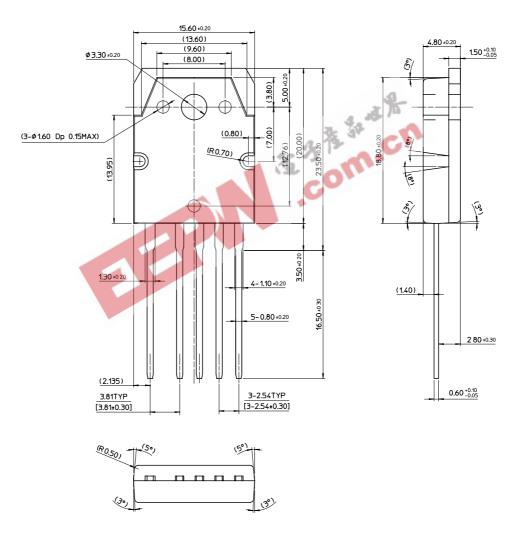


Figure 14. Static Drain-Source on Resistance



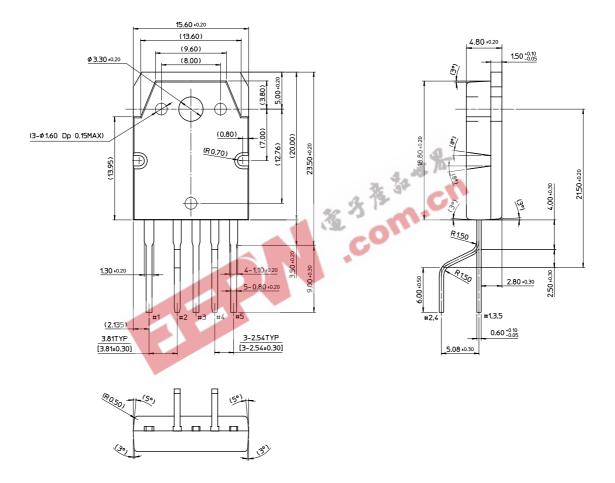
Package Dimensions



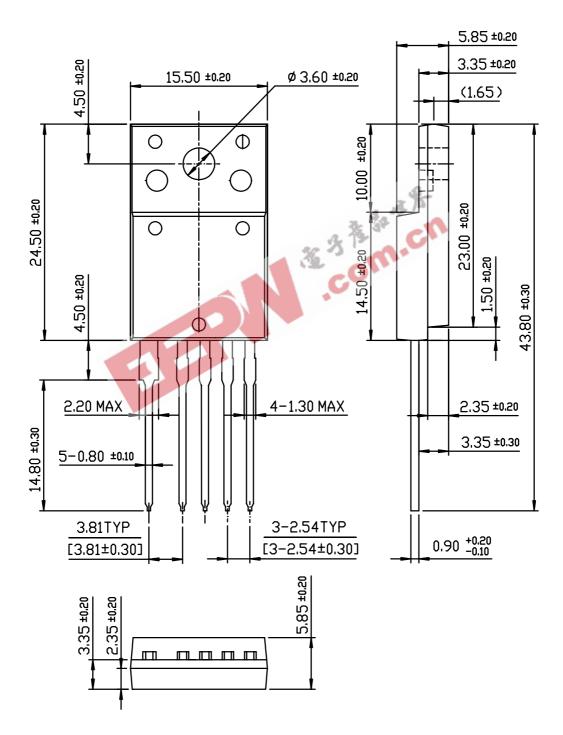


Package Dimensions (Continued)

TO-3P-5L (Forming)



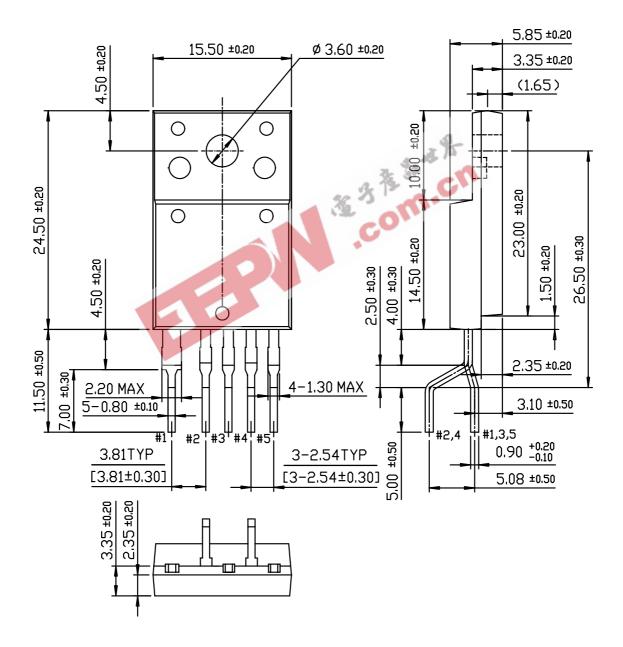
Package Dimensions (Continued)



TO-3PF-5L

Package Dimensions (Continued)

TO-3PF-5L(Forming)



Ordering Information

Product Number	Package	Operating Temperature
KA3S0680RB-TU	TO-3P-5L	-25°C to +85°C
KA3S0680RB-YDTU	TO-3P-5L(Forming)	-25 C 10 +65 C
KA3S0680RFB-TU	TO-3PF-5L	-25°C to +85°C
KA3S0680RFB-YDTU	TO-3PF-5L(Forming)	-25 C 10 +65 C

TU : Non Forming Type YDTU : Forming Type



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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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